PLASMA GENERATING ELECTRODE

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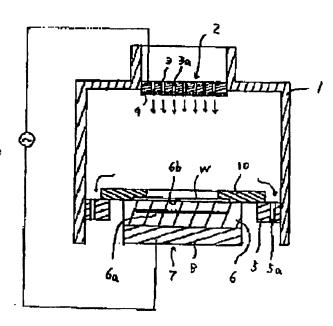
PROBLEM TO BE SOLVED: To provide a

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Abstract of JP11251093

plasma generating electrode that is hardly corroded even if it is exposed to plasma under a corrosive halogen gas, and can generate good quality plasma for a long time without giving adverse effect such as particles on a semiconductor wafer or the like.

SOLUTION: A plasma generating electrode 2 is composed by covering at least a part that is located on a conductive base body 3 formed from any of silicon(Si, carbon(C) and silicon carbide and is exposed to plasma under a corrosive halogen gas with a hard carbon film 4 formed from a material such as diamond-like carbon having an amorphous structure or a crystalline structure or diamond.



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